1A Step-Down DC-DC Converter ME3103

General Description

The ME3103 is a step-down current-mode, DC-DC converter. At heavy load, the constant-frequency PWM control performs excellent stability and transient response. To ensure the longest battery life in portable applications, the ME3103 provides a power-saving pulse -Skipping Modulation (PSM) mode to reduce quiescent current under light load operation to save power.

The ME3103 supports a range of input voltages from 2.5V to 5.5V, allowing the use of a single Li+/Li-polymer cell, multiple Alkaline/NiMH cell, USB, and other standard power sources. The output voltage is adjustable from 0.6V to the input voltage, while the part number suffix ME3103 indicates pre-set output voltage of 3.3V, 2.8V, 2.5V, 1.8V, 1.5V, 1.2V or adjustable. All versions employ internal power switch and synchronous rectifier for to minimize external part count and realize high efficiency. During shutdown, the input is disconnected from the output and the shutdown current is less than 0.1μA. Other key features include under-voltage lockout to prevent deep battery discharge.

Features

- Efficiency up to 96%
- Only 40μA (TYP.) Quiescent Current
- Output Current: Up to 1A
- Internal Synchronous Rectifier
- 1.5MHz Switching Frequency
- Soft Start
- Under-Voltage Lockout
- Short Circuit Protection
- Thermal Shutdown

Applications

- Cellular Phone
- Portable Electronics
- Wireless Devices
- Cordless Phone
- Computer Peripherals
- Battery Powered Widgets
- Electronic Scales
- Digital Frame

Package

- 5-pin   SOT23-5
- 6-pin   DFN2*2-6L
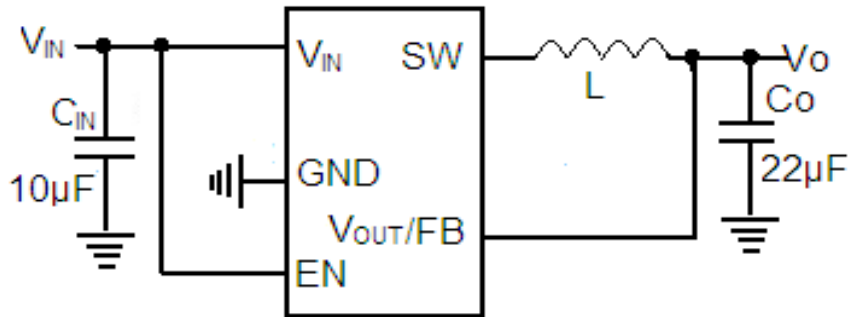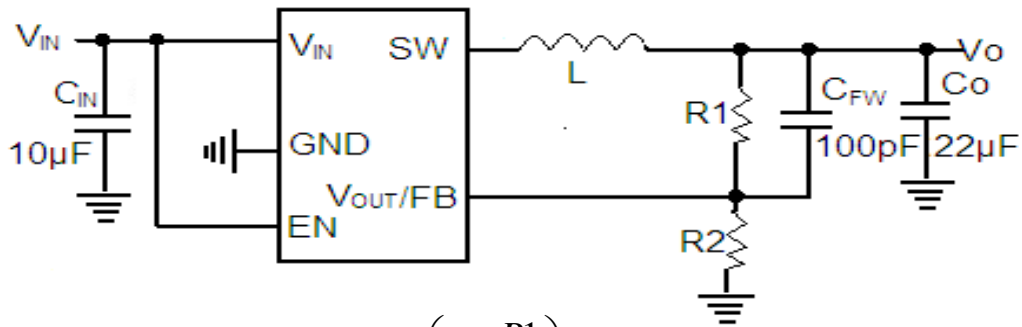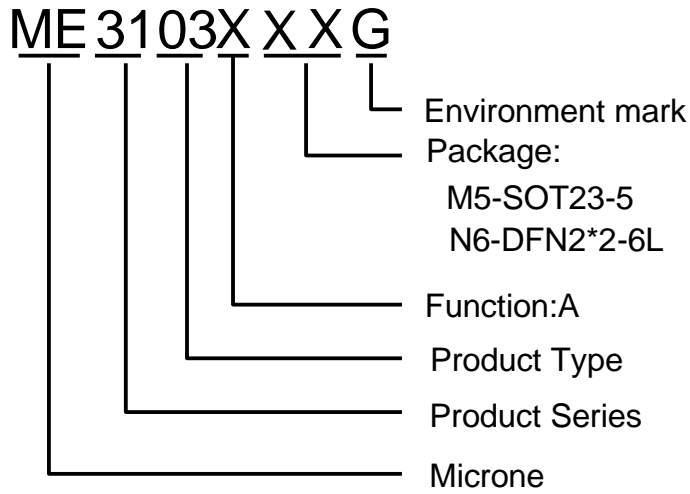
Typical Application

Fig1. Fixed Output Voltage

$$V_O = 0.6 \times \left(1 + \frac{R1}{R2}\right)$$

Fig2. Adjustable Output Voltage

Selection Guide

ME3103X X X G

- Environment mark
- Package:
  - M5-SOT23-5
  - N6-DFN2*2-6L
- Function:A
- Product Type
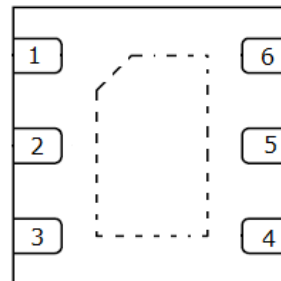- Product Series
- Microne

product series	product description
ME3103AM5G	VFB=0.6V；Package：SOT23-5
ME3103AN6G	VFB=0.6V； Package：DFN2*2-6L

Pin Configuration

MARK
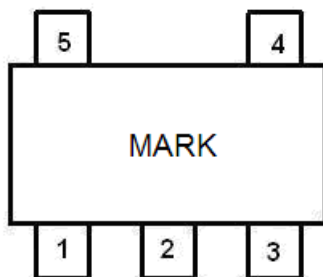
SOT23-5

DFN2*2-6L

Pin information

Pin Number（SOT23-5）	Pin Number（DFN2*2-6L）	Name	Function
1	3	EN	Chip Enable
2	6	GND	Ground
3	1	SW	Switch
4	5	V_{IN}	Input
5	4	FB	Feedback
	2	NC	No Connect

Block Diagram
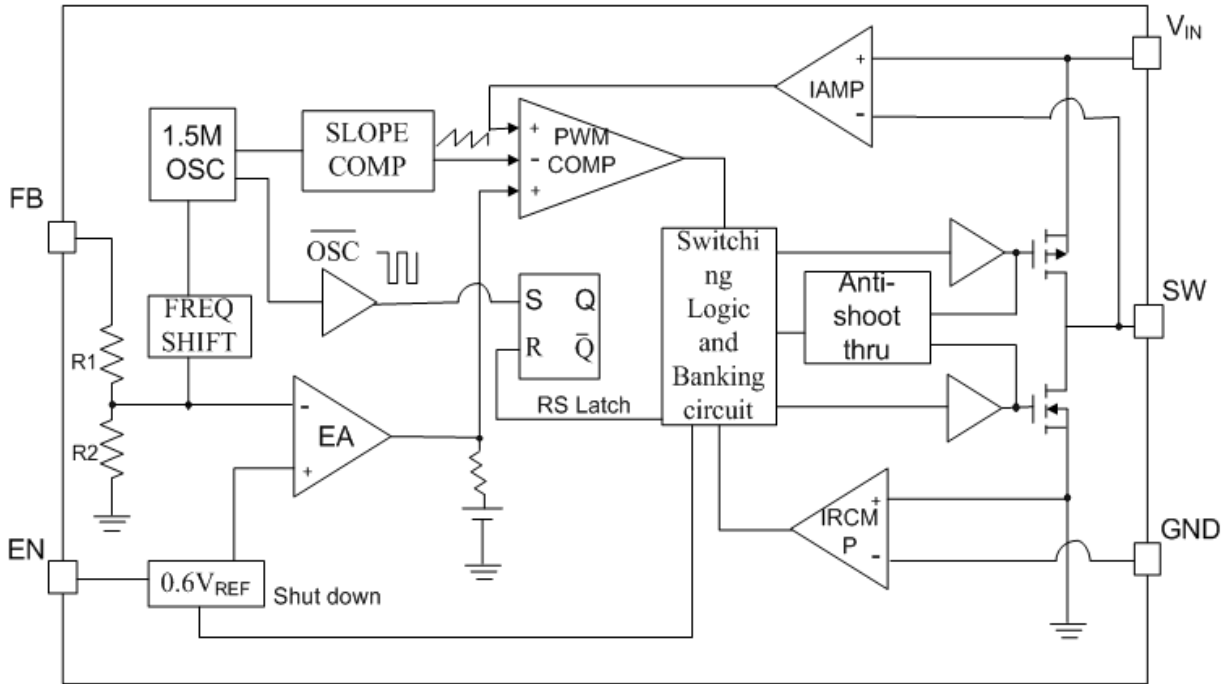
Absolute Maximum Ratings

Parameter	Symbol	Rating	Unit
Power supply voltage, V_{IN}	V_{IN}	$-0.3 \sim 6.0$	V
voltage at EN、FB Pin	V_{EN}, V_{FB}	$-0.3 \sim V_{IN}$	V
voltage at SW Pin	V_{SW}	$-0.3 \sim V_{IN} + 0.3$	V
Internal Power Dissipation, （SOT23-5）	P_D	300	mW
Operating Ambient Temperature	T_{opr}	$-40 \sim +150$	°C
Storage Temperature	T_{stg}	$-40 \sim +150$	°C
Soldering temperature and time	T_{solder}	260°C, 10S	°C

Electrical Characteristics

（V_{IN} = V_{EN}=3.6V, V_O=1.8V, C_{IN} =10μF, C_O =22μF, L=4.7μH, C_{FW} =100pF ,T_A =25 °C, unless otherwise noted.）

Parameter	Symbol	Test condition		Min	Typ.	Max	Unit
Input voltage range	V_{IN}			2.5	-	5.5	V
Regulated Feedback Voltage	V_{FB}			0.588	0.6	0.612	V
Reference Voltage Line Regulation	$\triangle V_{FB}$			-	0.3	-	%/V
Regulated Output Voltage Accuracy	V_O	I_O =100mA		-3	-	+3	%
Peak Inductor Current	I_{PK}	V_{IN} = V_{EN} =3V,V_{FB} =0.5V or V_o=90%		-	1.5	-	A
Output Voltage Line Regulation	LNR	V_{IN} =V_{EN}= 2.5V to 5V,I_o=10mA		-	0.2	0.5	%/V
Output Voltage Load Regulation	LDR	Io=1.0mA to 800mA		-	0.5	1.5	%
Quiescent Current	I_Q	No load		-	40	70	μA
Shutdown Current	I_{SD}	V_{EN}=0V		-	0.1	1	μA
Oscillator Frequency	F_{OSC}	V_O=100%		1.2	1.5	1.8	MHz
		V_{FB}=0V or V_O=0V			500		KHz
Drain-Source On-State Resistance	$R_{DS(ON)}$	I_{DS}=100mA	PMOS	-	0.3	0.45	Ω
			NMOS	-	0.35	0.5	Ω
SW Leakage Current	I_{LSW}			-	±0.01	1	μA
High Efficiency	η			-	96	-	%
EN Threshold High	V_{EH}			1.5	-	-	V
EN Threshold Low	V_{EL}			-	-	0.3	V
EN Leakage Current	I_{EN}			-	±0.01	1	μA
Over Temperature Protection	OTP			-	160	-	°C
OTP Hysteresis	OTH			-	40	-	°C

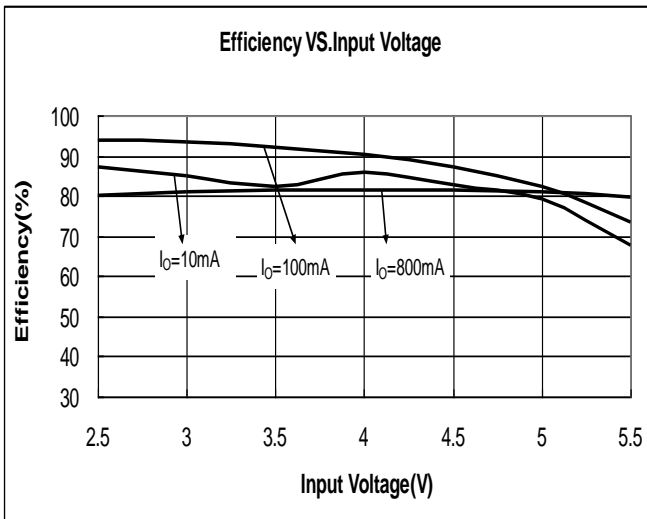## Typical Performance Characteristics
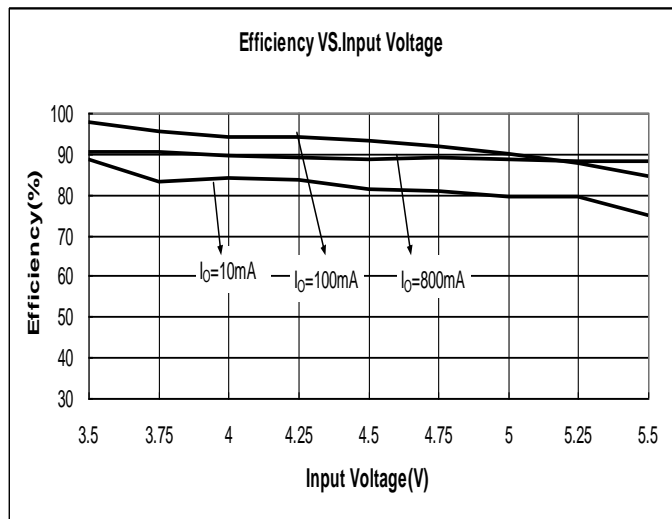
1. Efficiency VS Output Current   (V_O=1.8V)
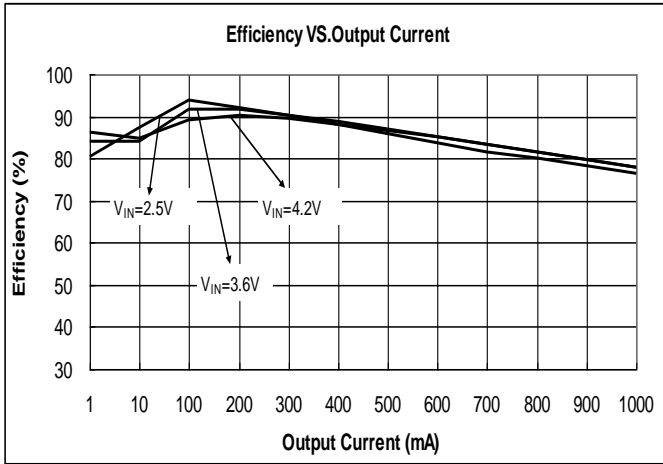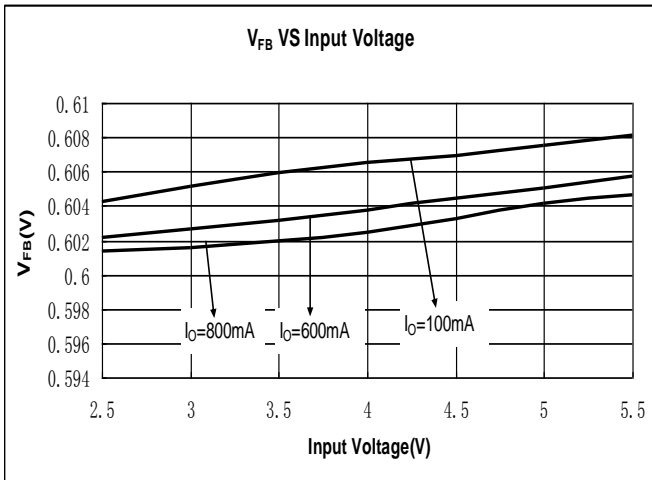
Efficiency VS Output Current   (V_O=3.3V)
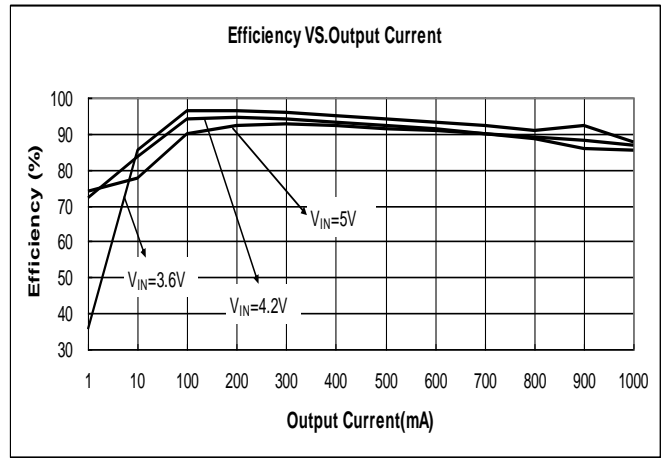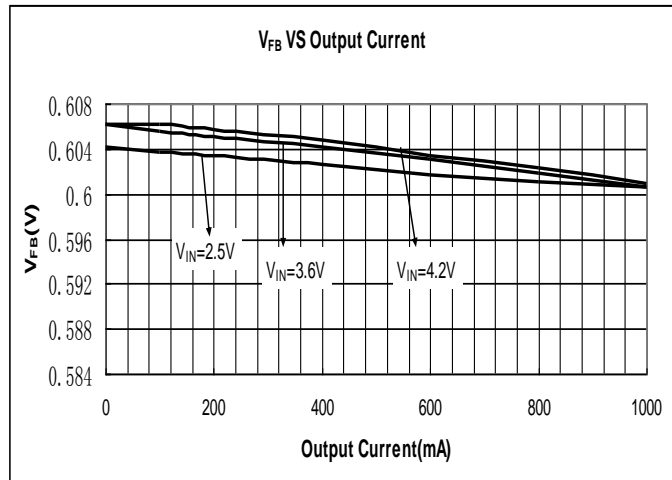

2. Efficiency VS Input Voltage (V_O=1.8V)

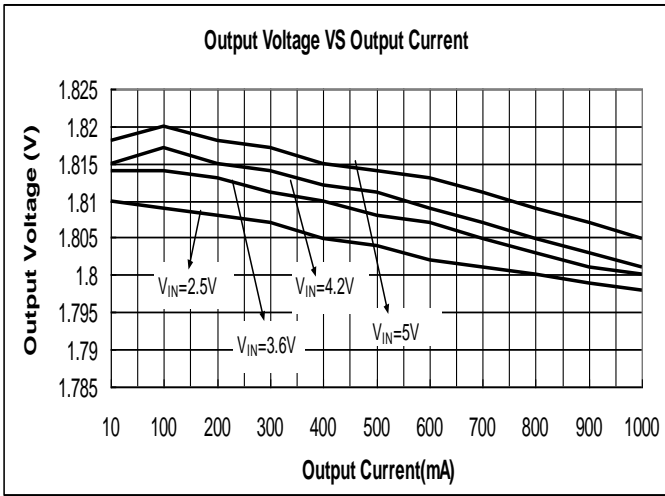Efficiency VS Input Voltage (V_O=3.3V)

3. V_{FB} VS Input Voltage

4. V_{FB} VS Output Current

5. Output Voltage VS Output Current(V_O=1.8V)

Output Voltage VS Output Current

Output Voltage (V) vs Output Current(mA)

V_{IN}=2.5V V_{IN}=4.2V V_{IN}=3.6V V_{IN}=5V

6. V_{FB} VS Temperature

V_{FB} VS Temperature

V_{FB}(V) vs Temperature(℃)

7. Dynamic Supply Current VS Input Voltage (V_O=1.8V)

Dynamic Supply Current VS Input Voltage
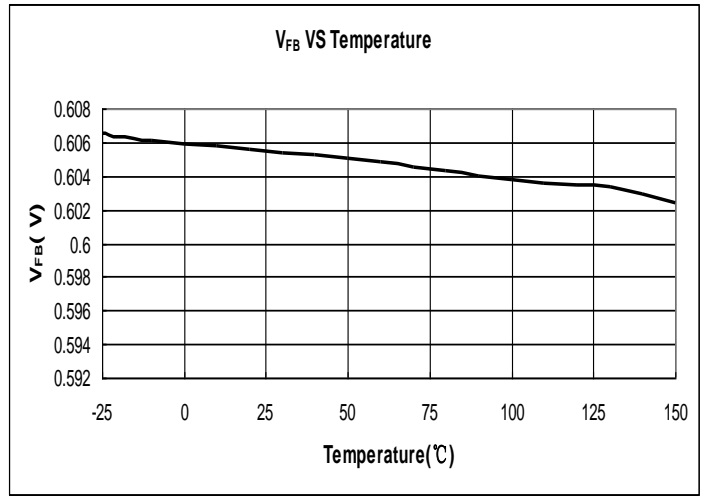
Supply Current(uA) vs Input Voltage(V)
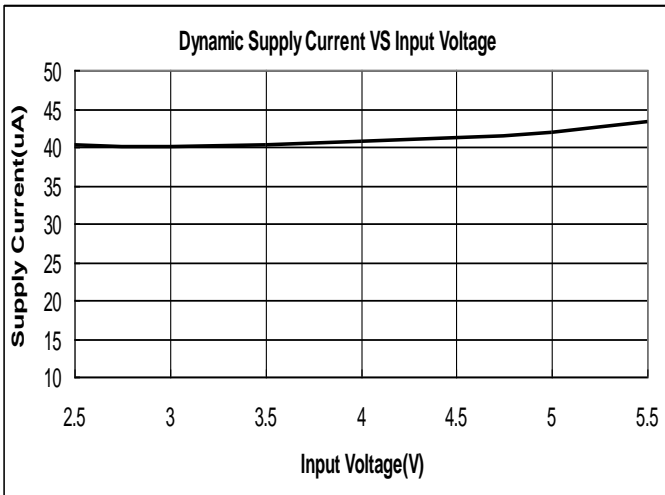
8. Dynamic Supply Current VS Temperature (V_{IN}=3.6V，V_O=1.8V)

Dynamic Supply Current VS Temperature

Dynamic Supply Current(uA) vs Temperature(℃)

9. Oscillator Frequency VS Input Voltage

Oscillator Frequency VS Input Voltage
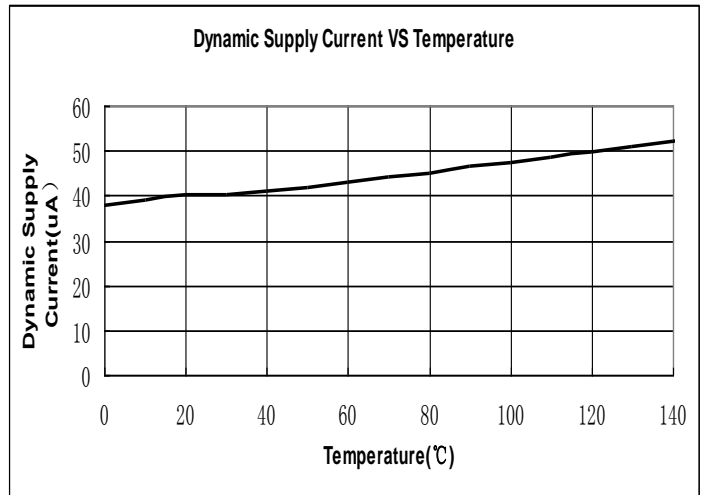
Oscillator Frequency (MHz) vs Input Voltage(V)
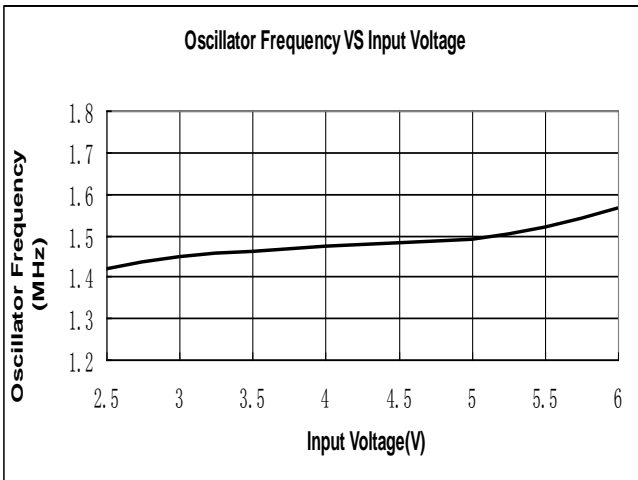
Application Information

The basic ME3103 application circuit is shown as up figures. External component selection is determined by the load requirement, selecting L first and then C_{IN} and C_{OUT}. It is better to use the patch ceramic capacitors at C_{OUT}.

Inductor Selection

For most applications, the value of the inductor will fall in the range of 1µH to 4.7µH. Its value is chosen based on the desired ripple current. Large value inductors lower ripple current and small value inductors result in higher ripple currents. Higher V_{IN} or V_{OUT} also increases the ripple current as shown in equation 1. A reasonable starting point for setting ripple current is $\triangle I_L$=400mA (40% of 1A).

$$\Delta I_L = \frac{1}{f \times L} V_{OUT} \left(1 - \frac{V_{OUT}}{V_{IN}} \right)$$

The DC current rating of the inductor should be at least equal to the maximum load current plus half the ripple current to prevent core saturation. Thus, a 1.4A rated inductor should be enough for most applications (1A + 400mA). For better efficiency, choose a low DC-resistance inductor.

V_O	1.2V	1.5V	1.8V	2.5V	3.3V
L	2.2µH	2.2µH	4.7µH	4.7µH	4.7µH

C_{IN} and C_{OUT} Selection

In continuous mode, the source current of the top MOSFET is a square wave of duty cycle V_{OUT}/V_{IN}. To prevent large voltage transients, a low ESR input capacitor sized for the maximum RMS current must be used. The maximum RMS capacitor current is given by: **CIN required** $I_{RMS} \cong I_{OMAX} \dfrac{[V_{OUT}(V_{IN} - V_{OUT})]^{1/2}}{V_{IN}}$

This formula has a maximum at $V_{IN}=2V_{OUT}$, where $I_{RMS}=I_{OUT}/2$. This simple worst-case condition is commonly used for design because even significant deviations do not offer much relief. Note that the capacitor manufacturer's ripple current ratings are often based on 2000 hours of life. This makes it advisable to further derate the capacitor, or choose a capacitor rated at a higher temperature than required. Consult the manufacturer if there is any question.

The selection of C_{OUT} is driven by the required effective series resistance (ESR). Typically, once the ESR requirement for C_{OUT} has been met, the RMS current rating generally far exceeds the I_{RIPPLE} (P-P) requirement. The output ripple $\triangle V_{OUT}$ is determined by:

$$\Delta V_{OUT} \cong \Delta I_L \left(ESR + \frac{1}{8fC_{OUT}} \right)$$

Where f = operating frequency, C_{OUT}=output capacitance and ΔI_L= ripple current in the inductor. For a fixed output

voltage, the output ripple is highest at maximum input voltage since ΔI increases with input voltage.

Using Ceramic Input and Output Capacitors

Higher values, lower cost ceramic capacitors are now becoming available in smaller case sizes. Their high ripple current, high voltage rating and low ESR make them ideal for switching regulator applications. Using ceramic capacitors can achieve very low output ripple and small circuit size.

When choosing the input and output ceramic capacitors, choose the X5R or X7R dielectric formulations. These dielectrics have the best temperature and voltage characteristics of all the ceramics for a given value and size.

Thermal consideration

Thermal protection limits power dissipation in the PAM2305. When the junction temperature exceeds 150°C, the OTP (Over Temperature Protection) starts the thermal shutdown and turns the pass transistor off. The pass transistor resumes operation after the junction temperature drops below 120°C.

For continuous operation, the junction temperature should be maintained below 125°C. The power dissipation is defined as:

$$P_D = I_O{}^2 \frac{V_O R_{DSONH} + (V_{IN} - V_O) R_{DSONL}}{V_{IN}} + (t_{SW} F_S I_O + I_Q) V_{IN}$$

I_Q is the step-down converter quiescent current. The term t_{SW} is used to estimate the full load step-down converter switching losses.

For the condition where the step-down converter is in dropout at 100% duty cycle, the total device dissipation reduces to:

$$P_D = I_O{}^2 R_{DSONH} + I_Q V_{IN}$$

Since $R_{DS(ON)}$, quiescent current, and switching losses all vary with input voltage, the total losses should be investigated over the complete input voltage range. The maximum power dissipation depends on the thermal resistance of IC package, PCB layout, the rate of surrounding airflow and temperature difference between junction and ambient. The maximum power dissipation can be calculated by the following formula:

$$P_D = \frac{T_{J(MAX)} - T_A}{\theta_{JA}}$$

Where $T_{J(max)}$ is the maximum allowable junction temperature 125°C. T_A is the ambient temperature and θ_{JA} is the thermal resistance from the junction to the ambient. Based on the standard JEDEC for a two layers thermal test board, the thermal resistance θ_{JA} of SOT23-5 package is 250°C/W. The maximum power dissipation at $T_A = 25$°C can be calculated by following formula: P =(125°C-25°C)/250°C/W=0.4W

Setting the Output Voltage

The internal reference is 0.6V (Typical). The output voltage is calculated as below:

$$V_O = 0.6 \times \left(1 + \frac{R1}{R2}\right)$$

The output voltage is given by Table 1.

Table 1: Resistor selection for output voltage setting

V$_O$ (V)	R1 (KΩ)	R2 (KΩ)
1.2	100	100
1.5	150	100
1.8	200	100
2.5	380	120
3.3	540	120

100% Duty Cycle Operation

As the input voltage approaches the output voltage, the converter turns the P-channel transistor continuously on. In this mode the output voltage is equal to the input voltage minus the voltage drop across the P- channel transistor:

$$V_{OUT} = V - I_{LOAD}\left(R_{DSON} + R_L\right)$$

where R$_{DSON}$= P-channel switch ON resistance, I$_{LOAD}$= Output current , R$_L$= Inductor DC resistance

UVLO and Soft-Start

The reference and the circuit remain reset until the V$_{IN}$ crosses its UVLO threshold. The ME3103 has an internal soft-start circuit that limits the in-rush current during start-up. This prevents possible voltage drops of the input voltage and eliminates the output voltage overshoot. The soft-start acts as a digital circuit to increase the switch current in several steps to the P-channel current limit (1500mA).

Short Circuit Protection

The switch peak current is limited cycle-by-cycle to a typical value of 1500mA. In the event of an output voltage short circuit, the device operates with a frequency of 400KHz and minimum duty cycle, therefore the average input current is typically 200mA.

Thermal Shutdown

When the die temperature exceeds 150°C, a reset occurs and the reset remains until the temperature decrease to 120°C, at which time the circuit can be restarted.

PCB Layout Check List

When laying out the printed circuit board, the following checklist should be used to ensure proper operation of the ME3103.

1. The power traces, consisting of the GND trace, the SW trace and the V_{IN} trace should be kept short, direct and wide.

2. Does the V_{FB} pin connect directly to the feedback resistors? The resistive divider R1/R2 must be connected between the (+) plate of C_{OUT} and ground.

3. Does the (+) plate of C_{IN} connect to V_{IN} as closely as possible? This capacitor provides the AC current to the internal power MOSFETs.

4. Keep the switching node, SW, away from the sensitive V_{FB} node.

5. Keep the (–) plates of C and C_{OUT} as close as possible.

Package Information

● **Package type:SOT23-5**
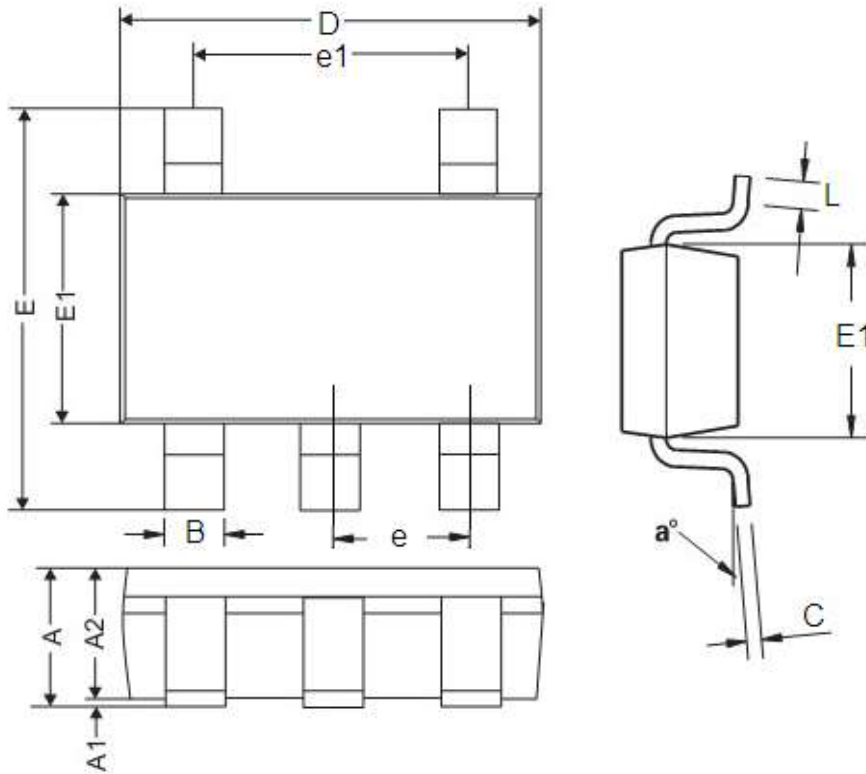
DIM	Dimension (mm)		Character	
	Min	**Max**	**Min**	**Max**
A	0.9	1.45	0.0354	0.0570
A1	0	0.15	0	0.0059
A2	0.9	1.3	0.0354	0.0511
B	0.2	0.5	0.0078	0.0196
C	0.09	0.26	0.0035	0.0102
D	2.7	3.10	0.1062	0.1220
E	2.2	3.2	0.0866	0.1181
E1	1.30	1.80	0.0511	0.0708
e	0.95REF		0.0374REF	
e1	1.90REF		0.0748REF	
L	0.10	0.60	0.0039	0.0236
a^0	0^0	30^0	0^0	30^0

● **Package type:DFN2*2-6L**

BOTTOM VIEW

TOP VIEW

SIDE VIEW
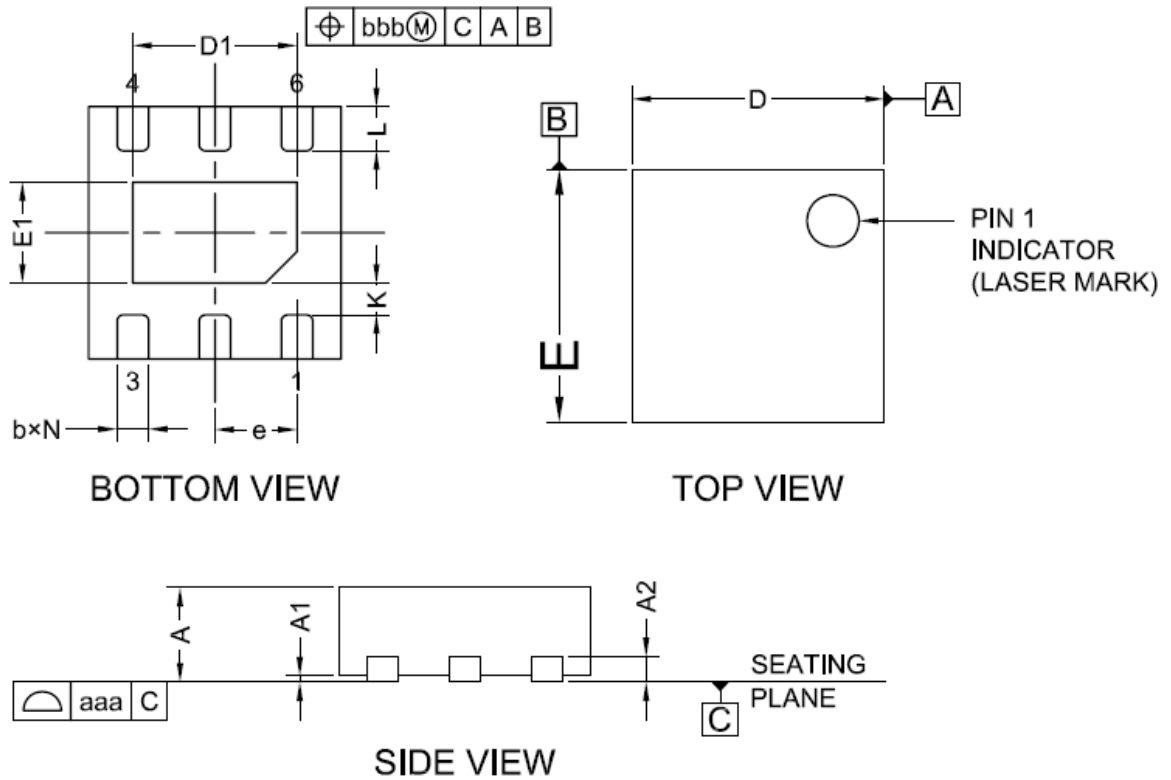
DIM	Dimension (mm)		
	Min	Typ	Max
A	0.70	0.75	0.80
A1	0.00	0.02	0.05
A2	0.203(Typ.)		
b	0.20	0.25	0.30
D	1.95	2.00	2.05
D1	1.20	1.30	1.40
E	1.95	2.00	2.05
E1	0.70	0.80	0.90
e	0.65bsc		
L	0.30	0.35	0.40
K	0.20 min		
N	6		
aaa	0.08		
bbb	0.10		